L Number	Hits	Search Text	DB	Time stamp
1	2732731	memory or storage	USPAT;	2004/03/01 14:41
			US-PGPUB;	
			ЕРО; ЈРО;	
			DERWENT	
2	1974	(memory or storage) and cell with float\$5 not gate	USPAT;	2004/03/01 14:42
			US-PGPUB;	
1			EPO; JPO;	
			DERWENT	
3	130	((memory or storage) and cell with float\$5 not gate) and cell with	USPAT;	2004/03/01 14:47
		transistor	US-PGPUB;	
			EPO; JPO;	
			DERWENT	
4	32	(((memory or storage) and cell with float\$5 not gate) and cell with	USPAT;	2004/03/01 14:43
		transistor) and pulse	US-PGPUB;	
İ			EPO; JPO;	
_			DERWENT	
5	98	(((memory or storage) and cell with float\$5 not gate) and cell with	USPAT;	2004/03/01 14:47
		transistor) not ((((memory or storage) and cell with float\$5 not gate) and	US-PGPUB;	
		cell with transistor) and pulse)	ЕРО; ЈРО;	
			DERWENT	

L Number	Hits	Search Text	DB	Time stamp
1	2732731	memory or storage	USPAT;	2004/03/01 15:03
			US-PGPUB;	
			EPO; JPO;	
2	1974	(memory or storage) and cell with float\$5 not gate	DERWENT USPAT;	2004/03/01 15:20
2	17/4	(memory of storage) and cent with months not gate	US-PGPUB;	2004/03/01 13.20
			ЕРО; ЛРО;	
			DERWENT	
3	130	((memory or storage) and cell with float\$5 not gate) and cell with	USPAT;	2004/03/01 14:47
		transistor	US-PGPUB;	
			EPO; JPO; DERWENT	
4	32	(((memory or storage) and cell with float\$5 not gate) and cell with	USPAT;	2004/03/01 14:43
,		transistor) and pulse	US-PGPUB;	200 1103701 1 1113
•		, -	ЕРО; ЈРО;	
			DERWENT	
5	98	(((memory or storage) and cell with float\$5 not gate) and cell with	USPAT;	2004/03/01 14:47
		transistor) not ((((memory or storage) and cell with float\$5 not gate) and cell with transistor) and pulse)	US-PGPUB; EPO; JPO;	
		con with transistory and pulsey	DERWENT	
6	274	((memory or storage) and cell with float\$5 not gate) and (static or sram)	USPAT;	2004/03/01 14:53
		, , , , , , , , , , , , , , , , , , , ,	US-PGPUB,	
			ЕРО; ЛРО;	
-	0	(((DERWENT	2004/02/01 14:54
7	8	(((memory or storage) and cell with float\$5 not gate) and (static or sram)) and 365/\$.ccls.	USPAT; US-PGPUB;	2004/03/01 14:54
		statil)) and 303/\$.ccis.	EPO; ЛРО;	
.			DERWENT	
8	54	((memory or storage) and cell with float\$5 not gate) and 365/\$.ccls.	USPAT;	2004/03/01 14:54
			US-PGPUB;	
			EPO; JPO; DERWENT	
9	805	(memory or storage) and cell with transistor with open	USPAT;	2004/03/01 15:08
_	303	(US-PGPUB;	200 1100/01 10:00
			ЕРО; ЛРО;	
			DERWENT	0004/00/01 15 55
10	430	((memory or storage) and cell with transistor with open) and 365/\$.ccls.	USPAT;	2004/03/01 15:13
			US-PGPUB; EPO; JPO;	
] [DERWENT	
11	36	((memory or storage) and cell with transistor with open) and	USPAT;	2004/03/01 15:13
		365/154.ccls.	US-PGPUB;	
			ЕРО; ЛРО;	
12	7681	(memory or storage) and cell with (source or drain) with float\$5	DERWENT USPAT;	2004/03/01 15:31
12	7001	(memory or storage) and cert with (source of drain) with floating	US-PGPUB;	2007103101 13.31
			ЕРО; ЛРО;	
			DERWENT	
13	3944	((memory or storage) and cell with (source or drain) with float\$5) and	USPAT;	2004/03/01 15:25
		365/\$.ccls.	US-PGPUB; EPO; JPO;	
			DERWENT	
14	41	((memory or storage) and cell with (source or drain) with float\$5) and	USPAT;	2004/03/01 15:25
		365/154.ccls.	US-PGPUB;	
			ЕРО; ЈРО;	
15	2100	(mamory or storage) and gell with transister with (DERWENT	2004/02/01 15:51
15	3198	(memory or storage) and cell with transistor with (source or drain) with float\$5	USPAT; US-PGPUB;	2004/03/01 15:51
		1104449	EPO; JPO;	
			DERWENT	
		·		

16	94	((memory or storage) and cell with transistor with (source or drain) with	USPAT;	2004/03/01 15:33
		float\$5) and source with electrically adj floating	US-PGPUB;	
			ЕРО; ЈРО;	
			DERWENT	
17	30	(((memory or storage) and cell with transistor with (source or drain)	USPAT;	2004/03/01 15:52
		with float\$5) and source with electrically adj floating) and pulse	US-PGPUB;	
			ЕРО; ЛРО;	
			DERWENT	
18	465	((memory or storage) and cell with transistor with (source or drain) with	USPAT;	2004/03/01 15:53
		float\$5) and pulse with gate	US-PGPUB;	
			ЕРО; ЈРО;	
	<u> </u>		DERWENT	